

## Features

- Switching transistor
- Ultra-small surface mount package
- Plastic-Encapsulate transistor



**SOT-23**

1. BASE
2. Emitter
3. COLLECTOR

## Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Max.	Unit
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Current-Continuous	$I_C$	600	mA
Collector Power Dissipation	$P_C$	300	mW
Typical Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	417	°C/W
Operating Junction Temperature Range	$T_J$	-55 To +150	°C
Storage Temperature Range	$T_{STG}$	-55 To +150	°C

**Electrical Characteristics** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(\text{BR})\text{CBO}}$	$I_C=100\mu\text{A}, I_E=0$	60	-	V
Collector-Emitter Breakdown Voltage	$V_{(\text{BR})\text{CEO}}$	$I_C=1\text{mA}, I_B=0$	40	-	V
Emitter-Base Breakdown Voltage	$V_{(\text{BR})\text{EBO}}$	$I_E=100\mu\text{A}, I_C=0$	6	-	V
Collector Cut-off Current	$I_{\text{CBO}}$	$V_{\text{CB}}=50\text{V}, I_E=0$	-	0.1	$\mu\text{A}$
Collector Cut-off Current	$I_{\text{CEX}}$	$V_{\text{CE}}=35\text{V}, V_{\text{EB}}=0.4\text{V}$	-	0.1	$\mu\text{A}$
Emitter Cut-off Current	$I_{\text{EBO}}$	$V_{\text{EB}}=5\text{V}, I_C=0$	-	0.1	$\mu\text{A}$
DC Current Gain	$h_{\text{FE}}^1$	$V_{\text{CE}}=1\text{V}, I_C=0.1\text{mA}$	20	-	-
	$h_{\text{FE}}^2$	$V_{\text{CE}}=1\text{V}, I_C=1\text{mA}$	40	-	-
	$h_{\text{FE}}^3$	$V_{\text{CE}}=1\text{V}, I_C=10\text{mA}$	80	-	-
	$h_{\text{FE}}^4$	$V_{\text{CE}}=1\text{V}, I_C=150\text{mA}$	100	300	-
	$h_{\text{FE}}^5$	$V_{\text{CE}}=2\text{V}, I_C=500\text{mA}$	40	-	-
Collector-Emitter Saturation Voltage	$V_{\text{CE}(\text{sat})}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	0.4	V
		$I_C=500\text{mA}, I_B=50\text{mA}$	-	0.75	V
Base-Emitter Saturation Voltage	$V_{\text{BE}(\text{sat})}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	0.95	V
		$I_C=500\text{mA}, I_B=50\text{mA}$	-	1.2	V
Transition Frequency	$f_T$	$V_{\text{CE}}=10\text{V}, I_C=20\text{mA}, F=100\text{MHz}$	250	-	MHz
Delay Time	$t_d$	$V_{\text{CC}}=30\text{V}, V_{\text{BE}(\text{off})}=-2\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$	-	15	nS
Rise Time	$t_r$		-	20	nS
Storage Time	$t_s$	$V_{\text{CC}}=30\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$	-	225	nS
Fall Time	$t_f$		-	60	nS

**Ratings and Characteristics Curves** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

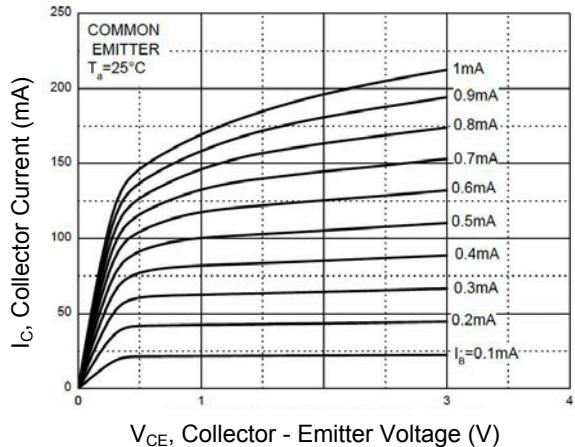


Figure 1. Static Characteristics

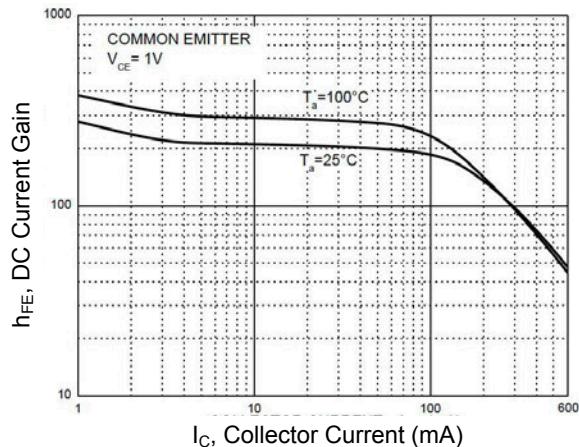


Figure 2. DC Current Gain vs. Collector Current

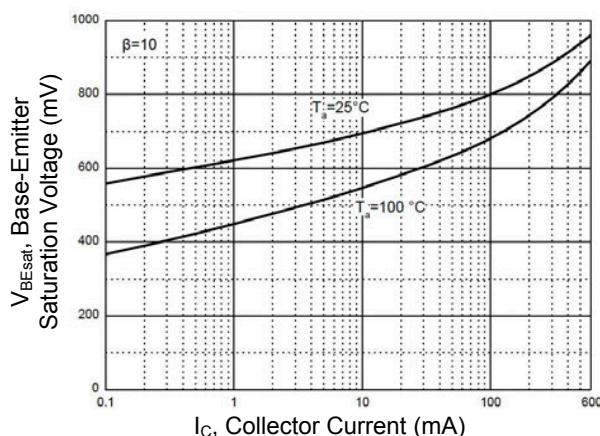


Figure 3. Base - Emitter Saturation Voltage vs.  
 Collector Current

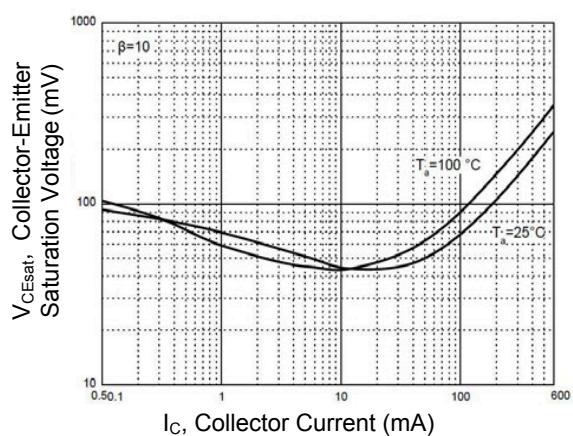


Figure 4. Collector - Emitter Saturation Voltage vs.  
 Collector Current

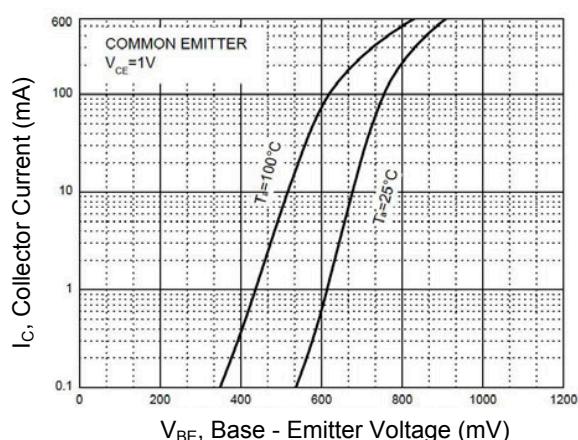


Figure 5. Collector Current vs. Base - Emitter Voltage

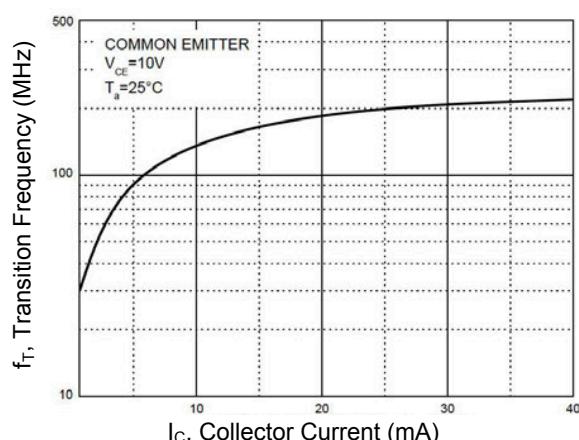


Figure 6. Transition Frequency vs. Collector Current

**Ratings and Characteristics Curves** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

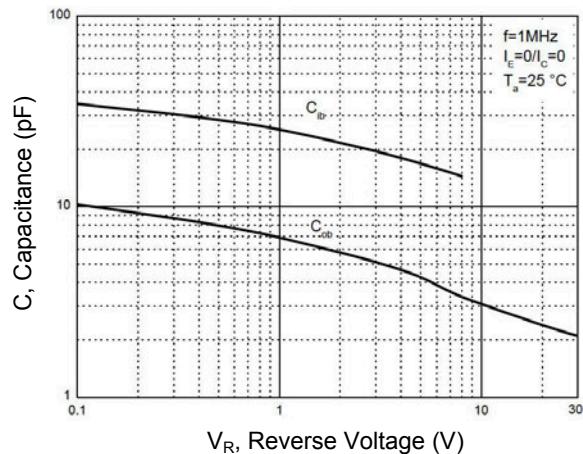


Figure 7. Capacitance Characteristics

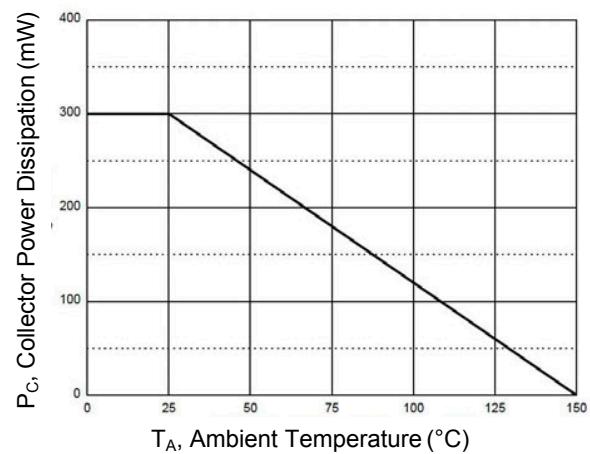
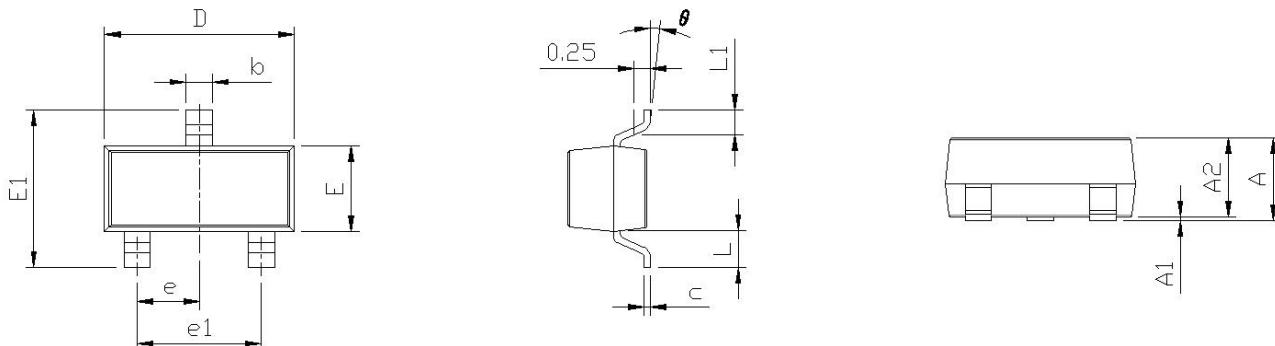


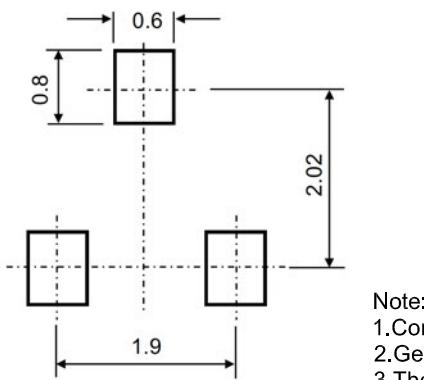
Figure 8. Power Dissipation vs Ambient Temperature

### Package Outline Dimensions (SOT-23)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

### Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05mm.
3. The pad layout is for reference purposes only.

### Ordering Information

Device	Package	Marking	Quantity	HSF Status
MMBT4401	SOT-23	2X	3,000pcs / Reel	RoHS Compliant